Iddo Amit

List of Publications by Year in descending order

23 papers	699 citations	687220 13 h-index	677027 22 g-index
23 all docs	23 docs citations	23 times ranked	1634 citing authors

#	Article	IF	Citations
1	Ultrahigh Performance Nanoengineered Grapheneâ€“Concrete Composites for Multifunctional Applications. Advanced Functional Materials, 2018, 28, 1705183.	7.8	161
2	High-Mobility and High-Optical Quality Atomically Thin WS 2. Scientific Reports, 2017, 7, 14911.	1.6	77
3	Specific and label-free femtomolar biomarker detection with an electrostatically formed nanowire biosensor. NPG Asia Materials, 2013, 5, e41-e41.	3.8	53
4	Laser-writable high-k dielectric for van der Waals nanoelectronics. Science Advances, 2019, 5, eaau0906.	4.7	51
5	Contact Doping of Silicon Wafers and Nanostructures with Phosphine Oxide Monolayers. ACS Nano, 2012, 6, 10311-10318.	7.3	50
6	Role of Charge Traps in the Performance of Atomically Thin Transistors. Advanced Materials, 2017, 29, 1605598.	11.1	46
7	Spatially Resolved Correlation of Active and Total Doping Concentrations in VLS Grown Nanowires. Nano Letters, 2013, 13, 2598-2604.	4.5	40
8	Strain-engineered inverse charge-funnelling in layered semiconductors. Nature Communications, 2018, 9, 1652.	5.8	36
9	Tunable diameter electrostatically formed nanowire for high sensitivity gas sensing. Nano Research, 2015, 8, 2206-2215.	5.8	35
10	Barrier Height Measurement of Metal Contacts to Si Nanowires Using Internal Photoemission of Hot Carriers. Nano Letters, 2013, 13, 6183-6188.	4.5	31
11	Parallel pâ€“n Junctions across Nanowires by One-Step Ex Situ Doping. ACS Nano, 2014, 8, 8357-8362.	7.3	31
12	Sub 20 meV Schottky barriers in metal/MoTe ₂ junctions. 2D Materials, 2018, 5, 025023.	2.0	18
13	Multiple State Electrostatically Formed Nanowire Transistors. IEEE Electron Device Letters, 2015, 36, 651-653.	2.2	17
14	Density and Energy Distribution of Interface States in the Grain Boundaries of Polysilicon Nanowire. Nano Letters, 2014, 14, 6190-6194.	4.5	14
15	Boron Monolayer Doping: Role of Oxide Capping Layer, Molecular Fragmentation, and Doping Uniformity at the Nanoscale. Advanced Materials Interfaces, 2020, 7, 1902198.	1.9	10
16	Functionalised hexagonal-domain graphene for position-sensitive photodetectors. Nanotechnology, 2017, 28, 124004.	1.3	9
17	Impact of Dopant Compensation on Graded pâ€“n Junctions in Si Nanowires. ACS Applied Materials & Interfaces, 2016, 8, 128-134.	4.0	8
18	Potential barrier height at the grain boundaries of a poly-silicon nanowire. Nanotechnology, 2015, 26, 355201.	1.3	4

#	Article	IF	Citations
19	Accurate Method To Determine the Mobility of Transition-Metal Dichalcogenides with Incomplete Gate Screening. ACS Applied Materials & Interfaces, 2019, 11, 44406-44412.	4.0	4
20	The Effect of Nonideal Polar Monolayers on Molecular Gated Transistors. ACS Applied Materials & Interfaces, 2010, 2, 2289-2292.	4.0	2
21	Molecular gating of transistors by amine-terminated layers. Applied Surface Science, 2012, 258, 4069-4072.	3.1	1
22	Energy dispersive spectroscopic measurement of charge traps in MoTe2. Physical Review B, 2019, 100, .	1.1	1
23	Photo-oxidized HfS2 - An embeddable and writable high-k dielectric for flexible Van der Waals nano-electronics. , 2018, , .		0